

## CYTHS124 GaAs HALL-EFFECT ELEMENTS

CYTHS124 Hall-effect element is a ion-implanted magnetic field sensor made of mono-crystal gallium arsenide (GaAs) semiconductor material group III-V using ion-implanted technology. It can convert a magnetic flux density signal linearly into voltage output.

HIGH STABILITY MOTOR CONTROL.

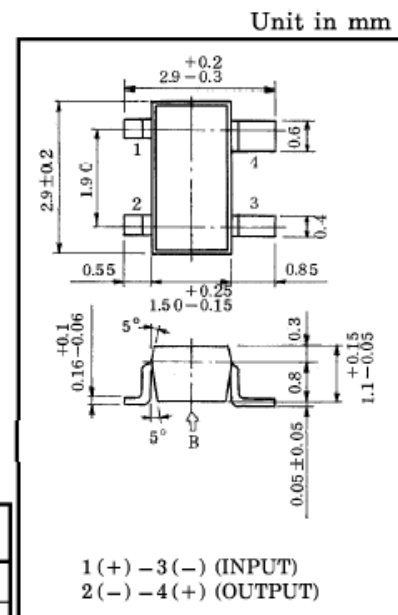
DIGITAL TACHOMETER.

CRANK SHAFT POSITION SENSOR.

- Excellent Temperature Characteristics.
- Wide Operating Temperature Range. (; -55~125°C)
- Excellent Output Voltage Linearity.
- High Internal Resistance. :  $R_d = 1000\Omega$  (Min.)
- Low Residual Voltage Ratio. :  $V_{HO} / V_H = \pm 5\%$  (Max.)

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Control Voltage	$V_C$	12	V
Power Dissipation	$P_D$	150	mW
Operating Temperature Range	$T_{opr}$	-55~125	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C



Unit weight: 0.013g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

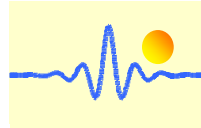
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Internal Resistance (Input)	$R_d$	$I_C = 1\text{mA}$	1000	1250	1500	$\Omega$
Residual Voltage Ratio	$V_{HO} / V_H$	$V_C = 5\text{V}, B = 0 / B = 0.1\text{T}$	—	—	$\pm 5$	%
Hall Voltage (Note 1)	$V_H$	$V_C = 5\text{V}, B = 0.1\text{T}$	130	150	170	mV
Temperature Coefficient (Note 2)	$V_{HT}$	$I_C = 5\text{mA}, B = 0.1\text{T}$ $T_1 = 25^\circ\text{C}, T_2 = 125^\circ\text{C}$	—	—	-0.06	% / °C
Linearity (Note 3)	$\Delta K_H$	$V_C = 5\text{V}, B_1 = 0.05\text{T}, B_2 = 0.1\text{T}$	—	—	2	%
Specific Sensitivity (Note 4)	$K^*$	$V_C = 5\text{V}, B = 0.1\text{T}$	—	30	—	$\times 10^{-2} / \text{T}$
Internal Resistance (Output)	$R_{OUT}$	$I_C = 1\text{mA}$	1800	2375	3000	$\Omega$

Note 1 :  $V_H = V_{HM} - V_{HO}$  ( $V_{HM}$  is meter indication)

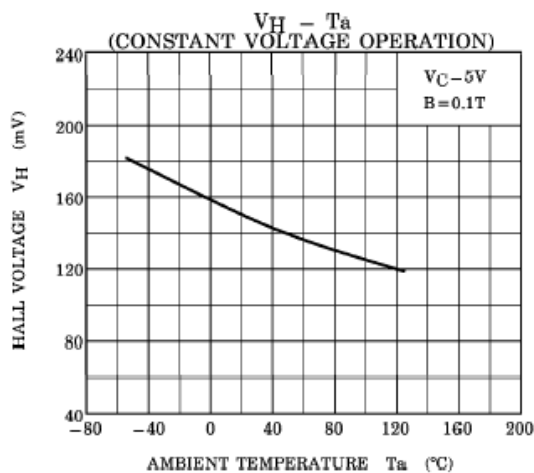
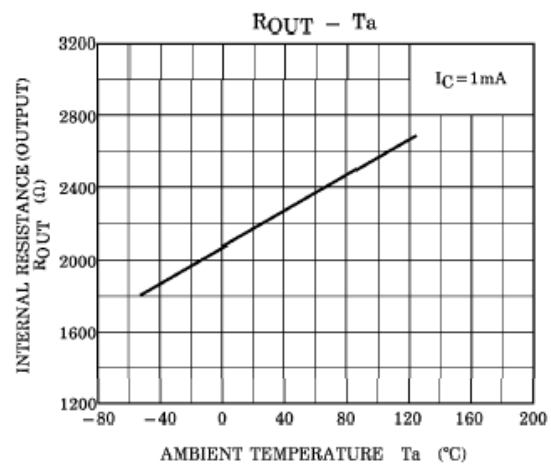
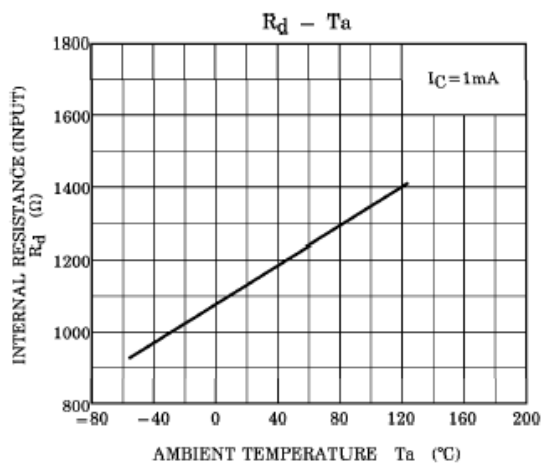
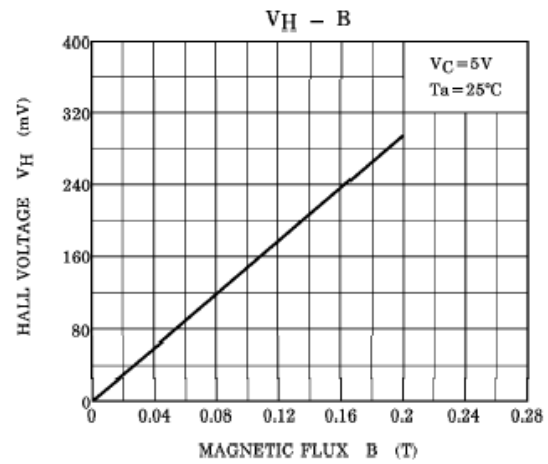
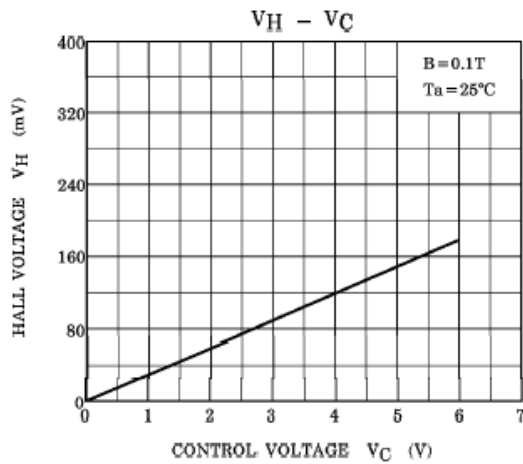
Note 2 :  $V_{HT} = \frac{1}{V_H(T_1)} \cdot \frac{V_H(T_2) - V_H(T_1)}{T_2 - T_1} \times 100 (\% / ^\circ\text{C})$   $V_{HO}$  : Residual Voltage

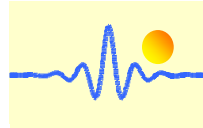
Note 3 :  $\Delta K_H = \frac{K_H(B_2) - K_H(B_1)}{1/2 \{K_H(B_1) + K_H(B_2)\}} \times 100 (\%)$ ,  $K_H = \frac{V_H}{I_C \cdot B}$   $K_H$  : Product Sensitivity

Note 4 :  $K^* = V_H / (R_d \times I_C \times B) = K_H / R_d$

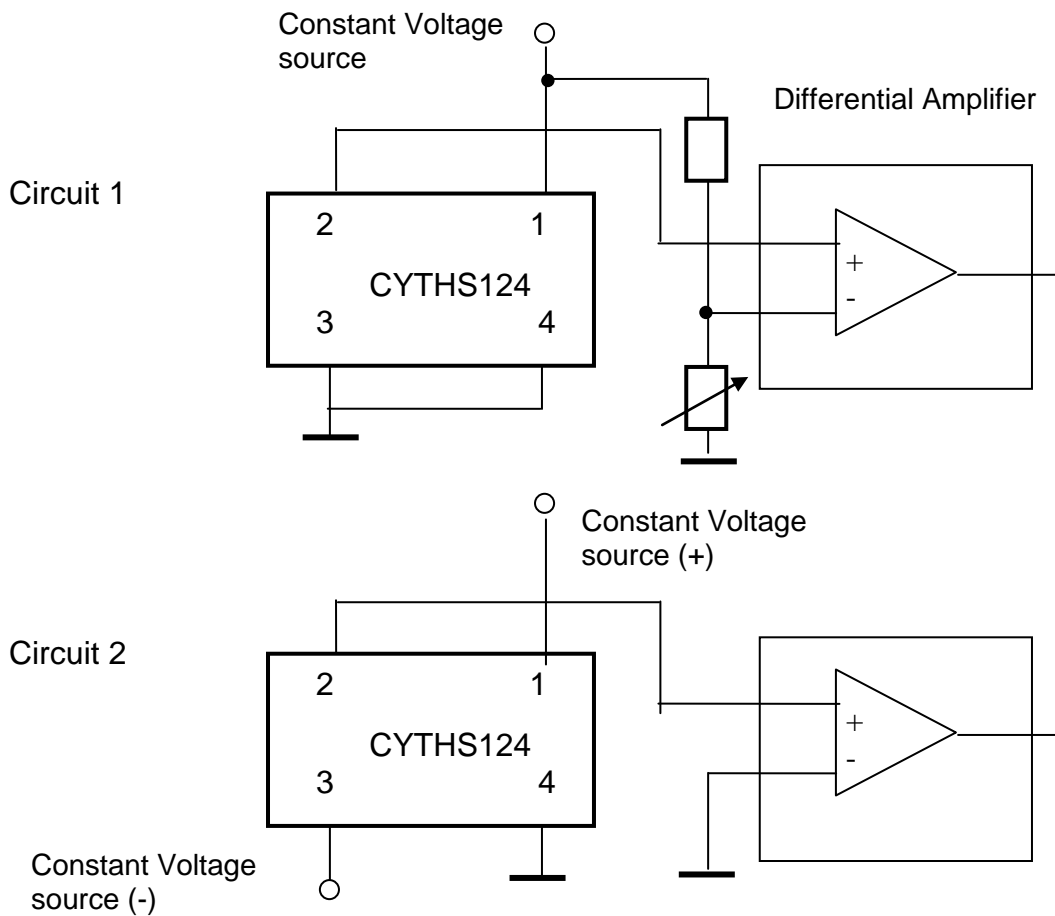


## Characteristics Curves





## Connection



## Application Notes

The Hall voltage  $V_H$  can be positive and negative. But if one connects the sensor as follows (circuit 1):

Pin 1: positive input voltage  $V_+$ , for instance +5VDC.  
Pin 3: GND  
Pin 2: OUTPUT  
Pin 4: GND

One can only measure the positive voltage at the pin 2. This means that the output voltage at zero magnetic field is not zero. This voltage is called as offset voltage. The output voltage in this case is not equal to the Hall voltage. The output voltage is equal to the sum of offset voltage and Hall voltage.

The offset voltage will be zero if you connect double power supplies  $V_+$  and  $V_-$  to the sensor (circuit 2):

Pin 1: positive input voltage  $V_+$ , for instance +5VDC.  
Pin 3: negative input voltage  $V_-$ , for instance -5VDC  
Pin 2: OUTPUT  
Pin 4: GND

In this case the output voltage is equal to the Hall Voltage.